PATENT ABSTRACTS OF JAPAN

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(71)Applicant : **TOKYO INST OF TECHNOL**

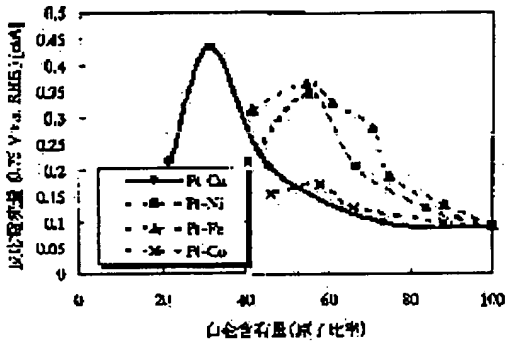
(72)Inventor : **OKAZAKI TAKESHI**
JINNAI AKINORI

(54) CATHODE CATALYST FOR SOLID POLYMER FUEL CELL AND SOLID POLYMER FUEL CELL

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a cathode catalyst for a solid polymer electrolyte fuel cell substantially reducing the amount of Pt used, and realizing remarkably high activity, and to provide a solid polymer fuel cell.

SOLUTION: This cathode catalyst for the solid polymer fuel cell is formed by retaining a Pt-Cu base alloy on conductive carbon. The Pt-Cu base alloy contains 20-40% Pt in the ratio of the number of atoms as a composition ratio. The Pt-Cu base alloy is a Pt-Cu alloy having Pt:Cu=3:7 in the ratio of the number of atoms as the composition ratio. The Pt-Cu base alloy is retained on the conductive carbon by high frequency sputtering.



LEGAL STATUS

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EUROPEAN PATENT OFFICE

(3)

Patent Abstracts of Japan

PUBLICATION NUMBER : 08100255
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APPLICATION NUMBER : 06261229

APPLICANT : MITSUBISHI MATERIALS CORP;

INVENTOR : KINOSHITA MAKOTO;

INT.CL. : C23C 14/34 C22C 21/00 H01L 29/40 H01L 29/43

TITLE : SPUTTERING TARGET MATERIAL FOR FORMING THIN FILM OF THIN FILM TRANSISTOR

ABSTRACT : PURPOSE: To obtain a sputtering target material generating a small number of particles and capable of forming a thin film less liable to cause unevenness in the alloying component content with the lapse of time.

CONSTITUTION: This sputtering target material has a compsn. consisting of 1-20wt.% one or more kinds of alloying components selected from among Nb, V, Ti, Zr, Ni, Pt and W and the balance Al with inevitable impurities and a recrystallized structure contg. an intermetallic compd. of Al with the alloying components dispersed as particles of ≤30μm average particle diameter in the matrix of ≤30μm average grain diameter. This target material can suppress the generation of particles during film formation.